

NTD5867NL

MOSFET – Power, N-Channel 60 V, 20 A, 39 mΩ

Features

- Low $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | | | Symbol | Value | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------|------------------------|-----------------------------------|------------|------|
| Drain-to-Source Voltage | | | V _{DSS} | 60 | V |
| Gate-to-Source Voltage – Continuous | | | V _{GS} | ±20 | V |
| Gate-to-Source Voltage – Non-Repetitive (t _p < 10 μs) | | | V _{GS} | ±30 | V |
| Continuous Drain Current (R _{θJC}) | Steady State | T _C = 25°C | I _D | 20 | A |
| | | T _C = 100°C | | 13 | |
| Power Dissipation (R _{θJC}) | | T _C = 25°C | P _D | 36 | W |
| Pulsed Drain Current | t _p = 10 μs | | I _{DM} | 76 | A |
| Operating Junction and Storage Temperature | | | T _J , T _{stg} | –55 to 150 | °C |
| Source Current (Body Diode) | | | I _S | 20 | A |
| Single Pulse Drain-to-Source Avalanche Energy (V _{DD} = 50 V, V _{GS} = 10 V, R _G = 25 Ω, I _{L(pk)} = 19 A, L = 0.1 mH, T _J = 25°C) | | | E _{AS} | 18 | mJ |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | | | T _L | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---------------------------------------------|-----------------|-------|--------------------|
| Junction-to-Case (Drain) | $R_{\theta JC}$ | 3.5 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 45 | |

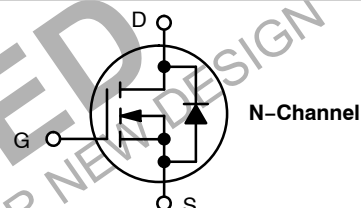
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).



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| $V_{(BR)DSS}$ | $R_{DS(on)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 60 V | 39 mΩ @ 10 V | 20 A |
| | 50 mΩ @ 4.5 V | 18 A |

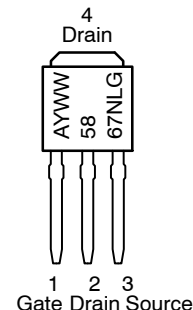
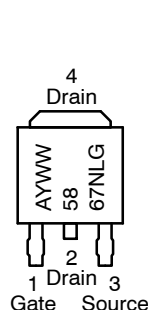


DPAK
CASE 369AA
(Surface Mount)
STYLE 2



IPAK
CASE 369D
(Straight Lead)
STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENT



A = Assembly Location*
Y = Year
WW = Work Week
5867NL = Device Code
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTD5867NL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|---------------------------|-----|-----------|----------------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 60 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | 60 | | mV/ $^\circ\text{C}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 1.0 | μA |
| | | | $T_J = 125^\circ\text{C}$ | | 100 | |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |

ON CHARACTERISTICS (Note 2)

| | | | | | | |
|--------------------------------------------|------------------|-------------------------------------------------|-----|-----|-----|----------------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 1.5 | 1.8 | 2.5 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 5.2 | | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ | | 26 | 39 | $\text{m}\Omega$ |
| | | $V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$ | | 33 | 50 | |
| Forward Transconductance | g_{FS} | $V_{DS} = 15\text{ V}, I_D = 10\text{ A}$ | | 8.0 | | S |

CHARGES, CAPACITANCES AND GATE RESISTANCES

| | | | | | | |
|------------------------------|--------------|------------------------------------------------------------------|--|-----|--|---------------|
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$ | | 675 | | μF |
| Output Capacitance | C_{oss} | | | 68 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 47 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}$ | | 15 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 1.0 | | |
| Gate-to-Source Charge | Q_{GS} | | | 2.2 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 4.3 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}$ | | 7.6 | | nC |
| Gate Resistance | R_G | | | 1.3 | | Ω |

SWITCHING CHARACTERISTICS (Note 3)

| | | | | | | |
|---------------------|--------------|------------------------------------------------------------------------------------------|--|------|--|----|
| Turn-On Delay Time | $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DD} = 48\text{ V}, I_D = 20\text{ A}, R_G = 2.5\text{ }\Omega$ | | 6.5 | | ns |
| Rise Time | t_r | | | 12.6 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 18.2 | | |
| Fall Time | t_f | | | 2.4 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|----------|------------------------------------------------------------------------------|---------------------------|-----|------|-----|----|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V}, I_S = 10\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.87 | 1.2 | V |
| | | | $T_J = 100^\circ\text{C}$ | | 0.78 | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 20\text{ A}$ | | 17 | | | ns |
| Charge Time | t_a | | | 13 | | | |
| Discharge Time | t_b | | | 4.0 | | | |
| Reverse Recovery Charge | Q_{RR} | | | 12 | | | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

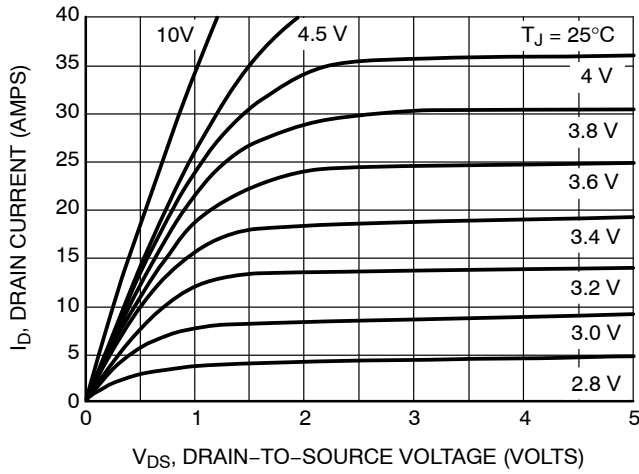


Figure 1. On-Region Characteristics

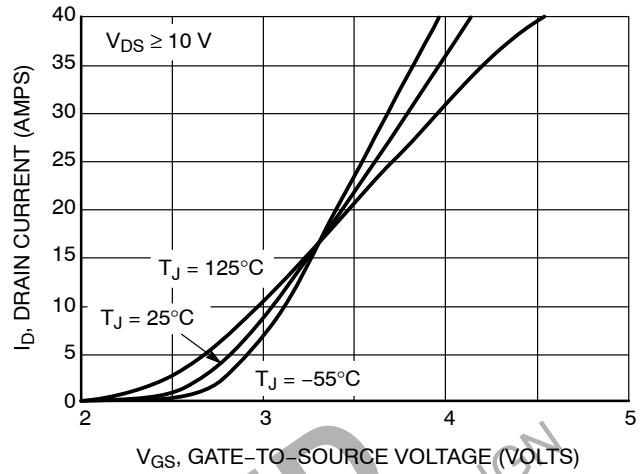


Figure 2. Transfer Characteristics

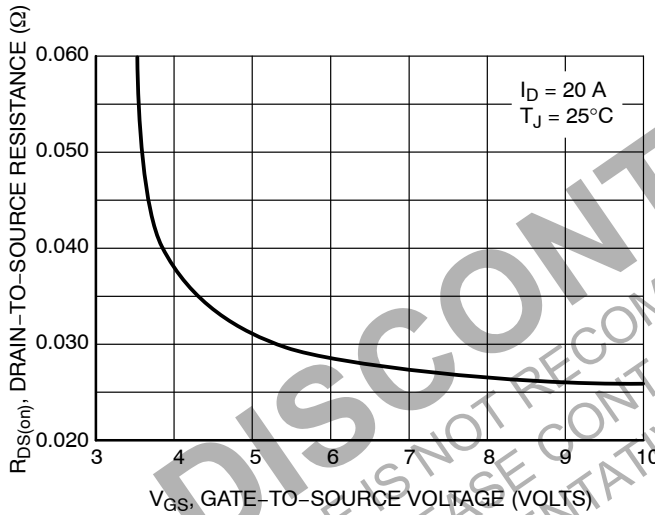


Figure 3. On-Resistance vs. Gate-to-Source Voltage

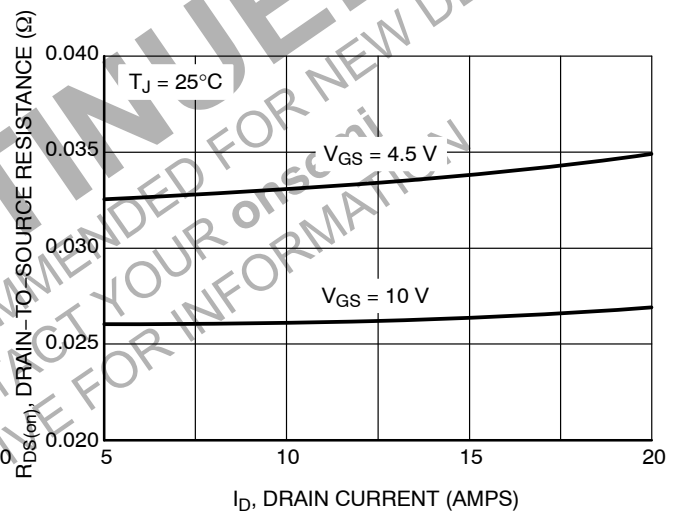


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

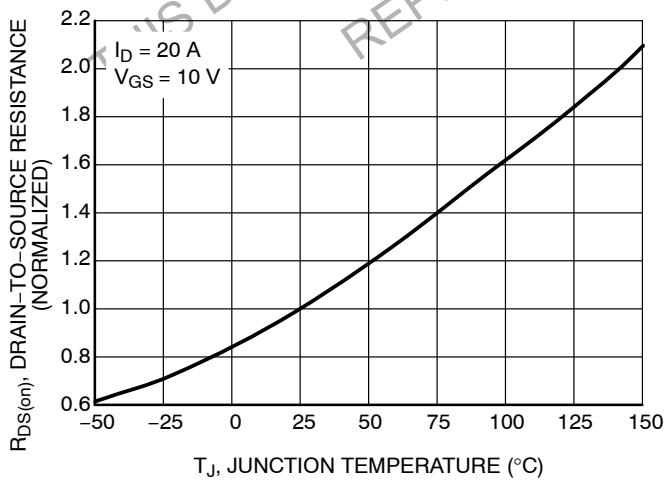


Figure 5. On-Resistance Variation with Temperature

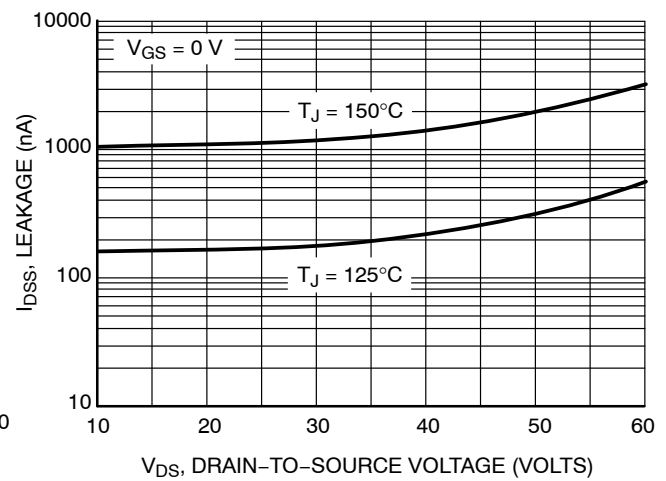


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

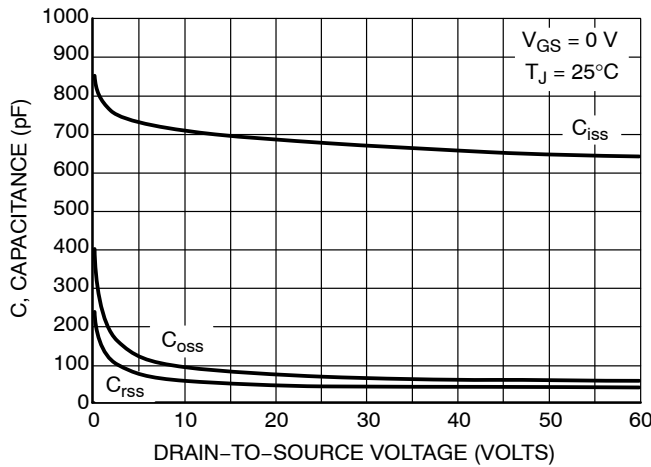


Figure 7. Capacitance Variation

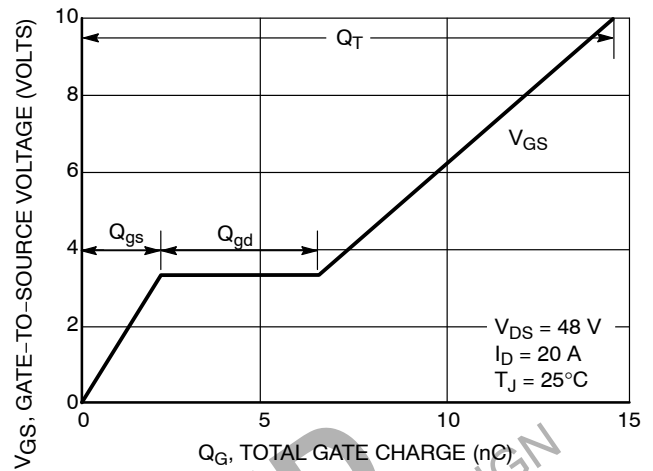


Figure 8. Gate-To-Source Voltage vs. Total Charge

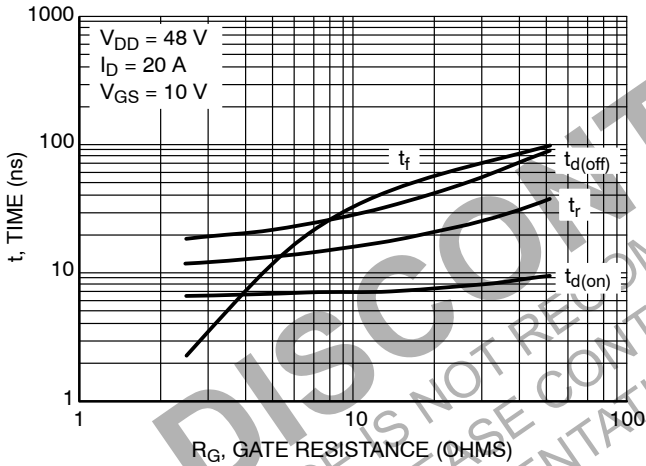


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

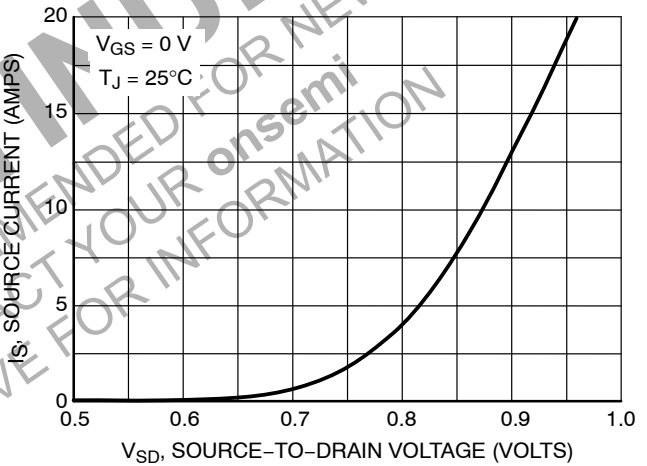


Figure 10. Diode Forward Voltage vs. Current

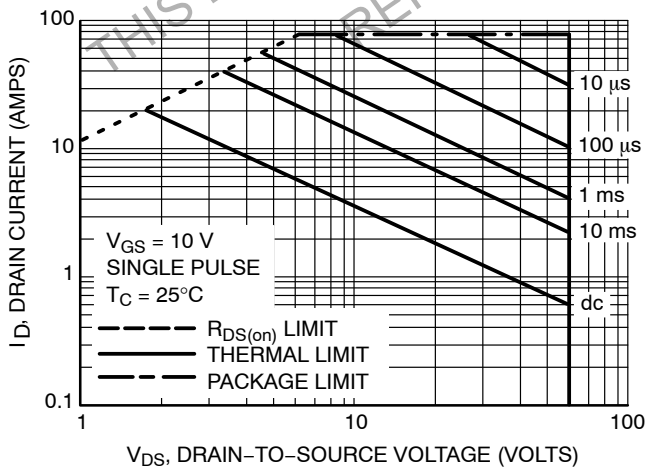


Figure 11. Maximum Rated Forward Biased Safe Operating Area

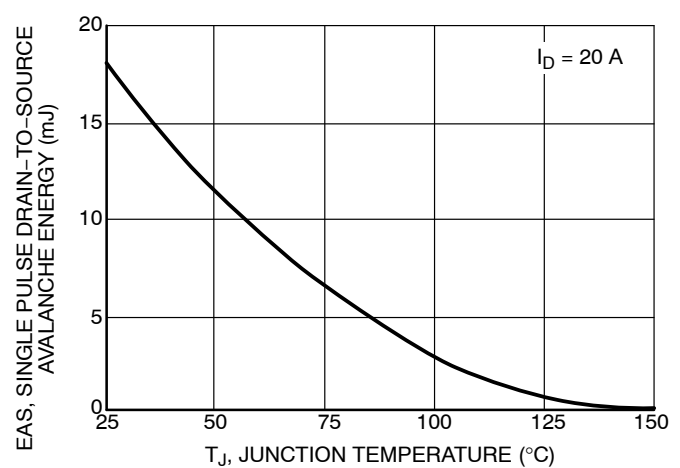
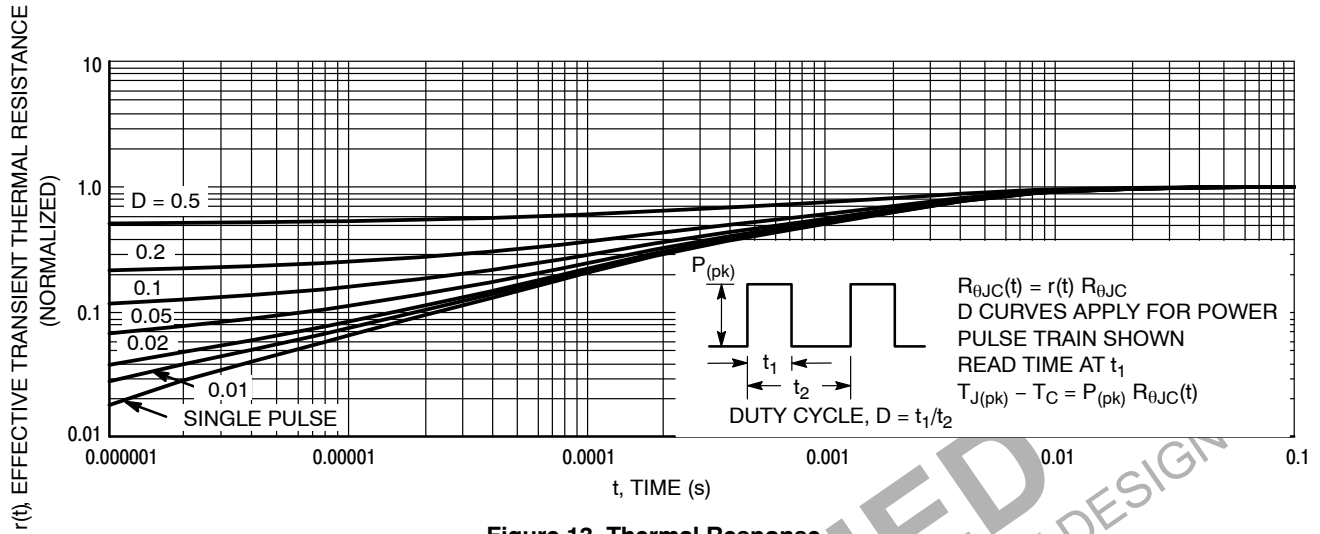


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL PERFORMANCE CURVES



ORDERING INFORMATION

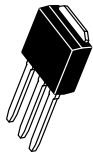
| Order Number | Package | Shipping [†] |
|--------------|-----------------------------------|-----------------------|
| NTD5867NL-1G | IPAK (Straight Lead) (Pb-Free) | 75 Units / Rail |
| NTD5867NLT4G | DPAK (Pb-Free) | 2500 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

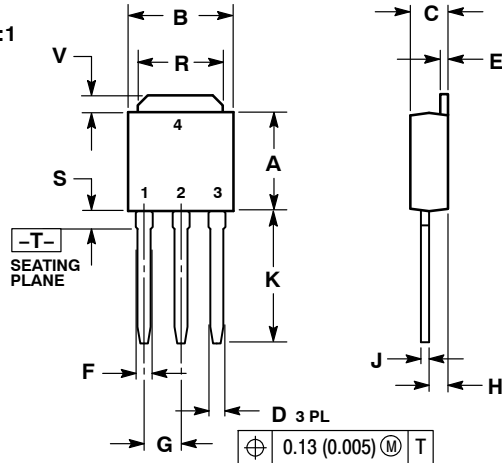
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IPAK CASE 369D-01 ISSUE C

DATE 15 DEC 2010

SCALE 1:1



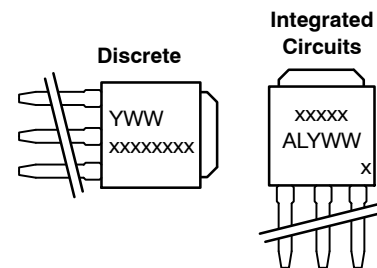
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | 0.235 | 0.245 | 5.97 | 6.35 |
| B | 0.250 | 0.265 | 6.35 | 6.73 |
| C | 0.086 | 0.094 | 2.19 | 2.38 |
| D | 0.027 | 0.035 | 0.69 | 0.88 |
| E | 0.018 | 0.023 | 0.46 | 0.58 |
| F | 0.037 | 0.045 | 0.94 | 1.14 |
| G | 0.090 BSC | | 2.29 BSC | |
| H | 0.034 | 0.040 | 0.87 | 1.01 |
| J | 0.018 | 0.023 | 0.46 | 0.58 |
| K | 0.350 | 0.380 | 8.89 | 9.65 |
| R | 0.180 | 0.215 | 4.45 | 5.45 |
| S | 0.025 | 0.040 | 0.63 | 1.01 |
| V | 0.035 | 0.050 | 0.89 | 1.27 |
| Z | 0.155 | --- | 3.93 | --- |

MARKING DIAGRAMS

- STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN
- STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE
- STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE
- STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2
- STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



xxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

| | | |
|------------------|-----------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION: | IPAK (DPAK INSERTION MOUNT) | PAGE 1 OF 1 |

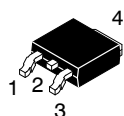
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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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ON



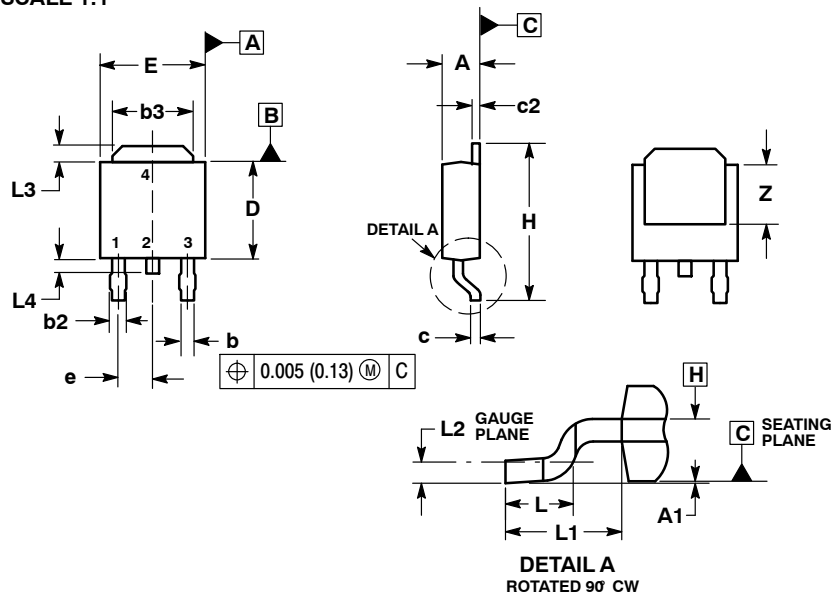
SCALE 1:1

DPAK (SINGLE GAUGE)

CASE 369AA-01

ISSUE B

DATE 03 JUN 2010



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.086 | 0.094 | 2.18 | 2.38 |
| A1 | 0.000 | 0.005 | 0.00 | 0.13 |
| b | 0.025 | 0.035 | 0.63 | 0.89 |
| b2 | 0.030 | 0.045 | 0.76 | 1.14 |
| b3 | 0.180 | 0.215 | 4.57 | 5.46 |
| c | 0.018 | 0.024 | 0.46 | 0.61 |
| c2 | 0.018 | 0.024 | 0.46 | 0.61 |
| D | 0.235 | 0.245 | 5.97 | 6.22 |
| E | 0.250 | 0.265 | 6.35 | 6.73 |
| e | 0.090 BSC | | 2.29 BSC | |
| H | 0.370 | 0.410 | 9.40 | 10.41 |
| L | 0.055 | 0.070 | 1.40 | 1.78 |
| L1 | 0.108 REF | | 2.74 REF | |
| L2 | 0.020 BSC | | 0.51 BSC | |
| L3 | 0.035 | 0.050 | 0.89 | 1.27 |
| L4 | | 0.040 | | 1.01 |
| Z | 0.155 | | 3.93 | |

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

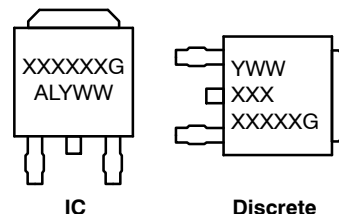
STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

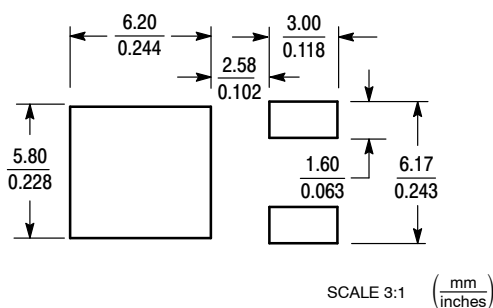
GENERIC MARKING DIAGRAM*



XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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